

Designer's™ Data Sheet
**Insulated Gate Bipolar Transistor
with Anti-Parallel Diode**
N-Channel Enhancement-Mode Silicon Gate

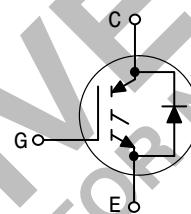
This Insulated Gate Bipolar Transistor (IGBT) is co-packaged with a soft recovery ultra-fast rectifier and uses an advanced termination scheme to provide an enhanced and reliable high voltage blocking capability. Short circuit rated IGBT's are specifically suited for applications requiring a guaranteed short circuit withstand time such as Motor Control Drives. Fast switching characteristics result in efficient operation at high frequencies. Co-packaged IGBT's save space, reduce assembly time and cost.

- Industry Standard High Power TO-264 Package (TO-3PBL)
- High Speed E_{off} : 160 μ J per Amp typical at 125°C
- High Short Circuit Capability – 10 μ s minimum
- Soft Recovery Free Wheeling Diode is included in the package
- Robust High Voltage Termination
- Robust RBSOA

MGY20N120D

Motorola Preferred Device

IGBT & DIODE IN TO-264
20 A @ 90°C
28 A @ 25°C
1200 VOLTS
SHORT CIRCUIT RATED



CASE 340G-02
STYLE 5
TO-264

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	1200	Vdc
Collector-Gate Voltage ($R_{GE} = 1.0 \text{ M}\Omega$)	V_{CGR}	1200	Vdc
Gate-Emitter Voltage — Continuous	V_{GE}	± 20	Vdc
Collector Current — Continuous @ $T_C = 25^\circ\text{C}$ — Continuous @ $T_C = 90^\circ\text{C}$ — Repetitive Pulsed Current (1)	I_{C25} I_{C90} I_{CM}	28 20 56	Adc Apc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	174 1.39	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Short Circuit Withstand Time ($V_{CC} = 720 \text{ Vdc}$, $V_{GE} = 15 \text{ Vdc}$, $T_J = 125^\circ\text{C}$, $R_G = 20 \Omega$)	t_{sc}	10	μs
Thermal Resistance — Junction to Case – IGBT — Junction to Case – Diode — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JC}$ $R_{\theta JA}$	0.7 1.1 35	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	260	$^\circ\text{C}$
Mounting Torque, 6-32 or M3 screw	10 lbf-in (1.13 N•m)		

(1) Pulse width is limited by maximum junction temperature. Repetitive rating.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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Preferred devices are Motorola recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-to-Emitter Breakdown Voltage (V _{GE} = 0 Vdc, I _C = 25 µAdc) Temperature Coefficient (Positive)	V _{(BR)CES}	1200 —	— 870	—	Vdc mV/°C
Zero Gate Voltage Collector Current (V _{CE} = 1200 Vdc, V _{GE} = 0 Vdc) (V _{CE} = 1200 Vdc, V _{GE} = 0 Vdc, T _J = 125°C)	I _{CES}	— —	— —	100 2500	µAdc
Gate-Body Leakage Current (V _{GE} = ± 20 Vdc, V _{CE} = 0 Vdc)	I _{GES}	—	—	250	nAdc
ON CHARACTERISTICS (1)					
Collector-to-Emitter On-State Voltage (V _{GE} = 15 Vdc, I _C = 10 Adc) (V _{GE} = 15 Vdc, I _C = 10 Adc, T _J = 125°C) (V _{GE} = 15 Vdc, I _C = 20 Adc)	V _{CE(on)}	— — —	2.42 2.36 2.90	3.54 — 4.99	Vdc
Gate Threshold Voltage (V _{CE} = V _{GE} , I _C = 1.0 mA) Threshold Temperature Coefficient (Negative)	V _{GE(th)}	4.0 —	6.0 10	8.0 —	Vdc mV/°C
Forward Transconductance (V _{CE} = 10 Vdc, I _C = 20 Adc)	g _{fe}	—	12	—	Mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V _{CE} = 25 Vdc, V _{GE} = 0 Vdc, f = 1.0 MHz)	C _{ies}	—	1876	—
Output Capacitance		C _{oes}	—	208	—
Transfer Capacitance		C _{res}	—	31	—
SWITCHING CHARACTERISTICS (1)					
Turn-On Delay Time	(V _{CC} = 720 Vdc, I _C = 20 Adc, V _{GE} = 15 Vdc, L = 300 µH R _G = 20 Ω) Energy losses include "tail"	t _{d(on)}	—	88	—
Rise Time		t _r	—	103	—
Turn-Off Delay Time		t _{d(off)}	—	190	—
Fall Time		t _f	—	284	—
Turn-Off Switching Loss		E _{off}	—	1.65	2.75
Turn-On Switching Loss		E _{on}	—	2.42	3.75
Total Switching Loss		E _{ts}	—	4.07	6.50
Turn-On Delay Time	(V _{CC} = 720 Vdc, I _C = 20 Adc, V _{GE} = 15 Vdc, L = 300 µH R _G = 20 Ω, T _J = 125°C) Energy losses include "tail"	t _{d(on)}	—	83	—
Rise Time		t _r	—	107	—
Turn-Off Delay Time		t _{d(off)}	—	216	—
Fall Time		t _f	—	494	—
Turn-Off Switching Loss		E _{off}	—	3.19	—
Turn-On Switching Loss		E _{on}	—	4.26	—
Total Switching Loss		E _{ts}	—	7.45	—
Gate Charge	(V _{CC} = 720 Vdc, I _C = 20 Adc, V _{GE} = 15 Vdc)	Q _T	—	63	—
		Q ₁	—	20	—
		Q ₂	—	27	—
DIODE CHARACTERISTICS					
Diode Forward Voltage Drop (I _{EC} = 10 Adc) (I _{EC} = 10 Adc, T _J = 125°C) (I _{EC} = 20 Adc)	V _{FEC}	— — —	2.92 1.73 3.67	3.59 — 4.57	Vdc

(1) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.

(continued)

ELECTRICAL CHARACTERISTICS — continued ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
DIODE CHARACTERISTICS — continued					
Reverse Recovery Time	$(I_F = 20 \text{ Adc}, V_R = 720 \text{ Vdc}, dI_F/dt = 150 \text{ A}/\mu\text{s})$	t_{rr}	—	114	—
		t_a	—	74	—
		t_b	—	40	—
		Q_{RR}	—	0.68	—
Reverse Recovery Stored Charge					μC
Reverse Recovery Time	$(I_F = 20 \text{ Adc}, V_R = 720 \text{ Vdc}, dI_F/dt = 150 \text{ A}/\mu\text{s}, T_J = 125^\circ\text{C})$	t_{rr}	—	224	—
		t_a	—	149	—
		t_b	—	75	—
		Q_{RR}	—	2.40	—
Reverse Recovery Stored Charge					μC
INTERNAL PACKAGE INDUCTANCE					
Internal Emitter Inductance (Measured from the emitter lead 0.25" from package to emitter bond pad)	L_E	—	13	—	nH

TYPICAL ELECTRICAL CHARACTERISTICS

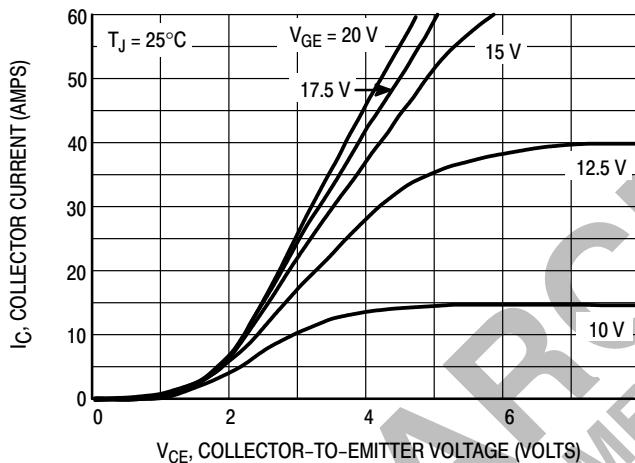


Figure 1. Output Characteristics

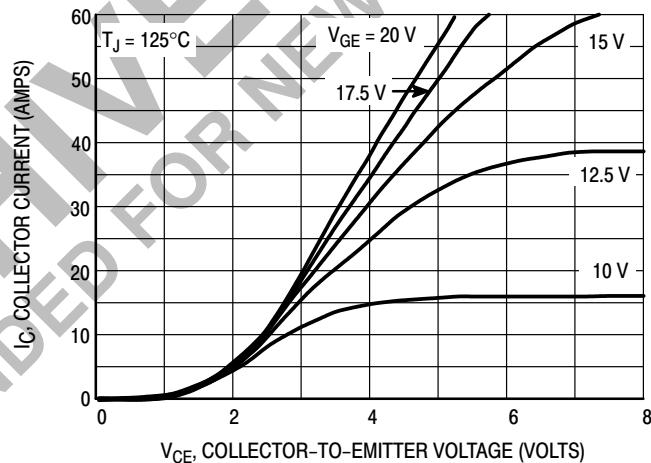


Figure 2. Output Characteristics

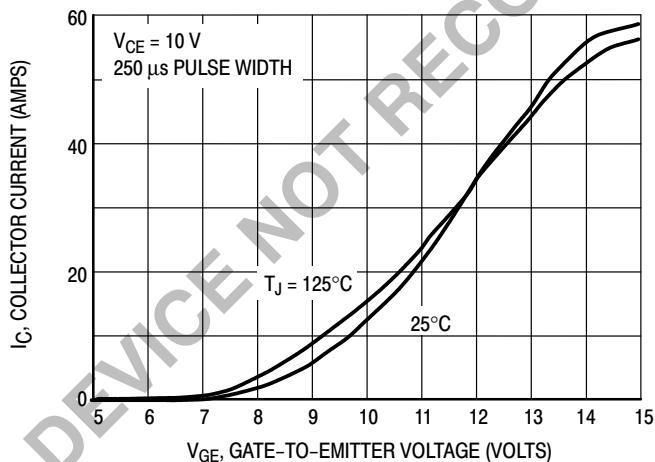


Figure 3. Transfer Characteristics

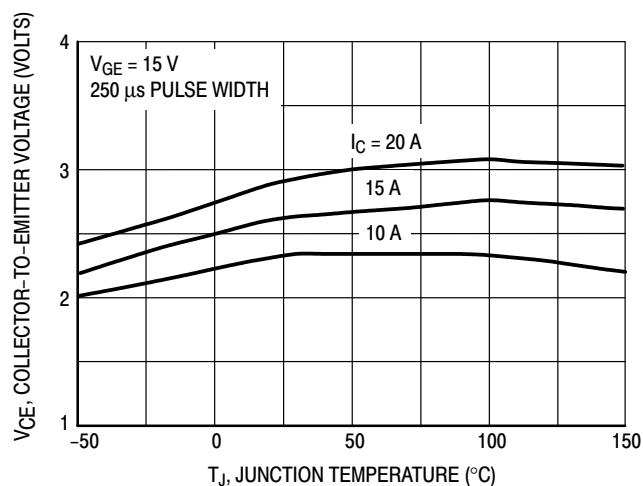


Figure 4. Collector-to-Emitter Saturation Voltage versus Junction Temperature

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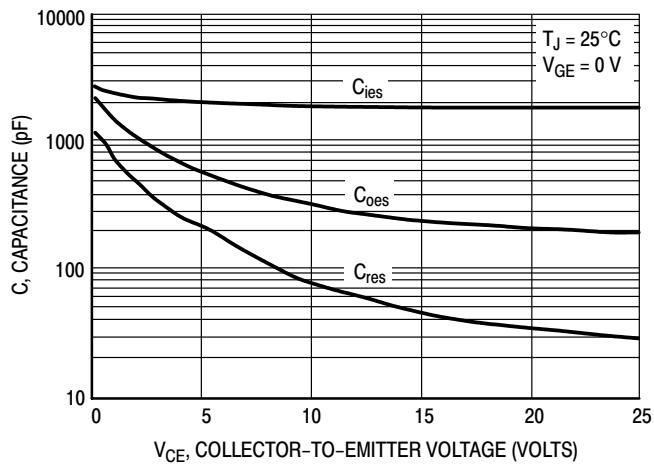


Figure 5. Capacitance Variation

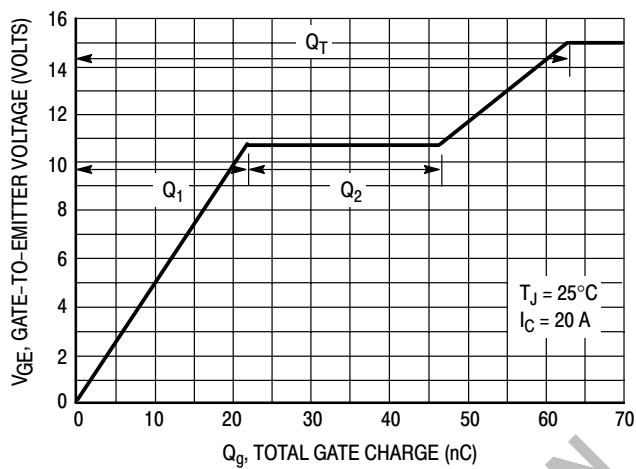


Figure 6. Gate-to-Emitter Voltage versus Total Charge

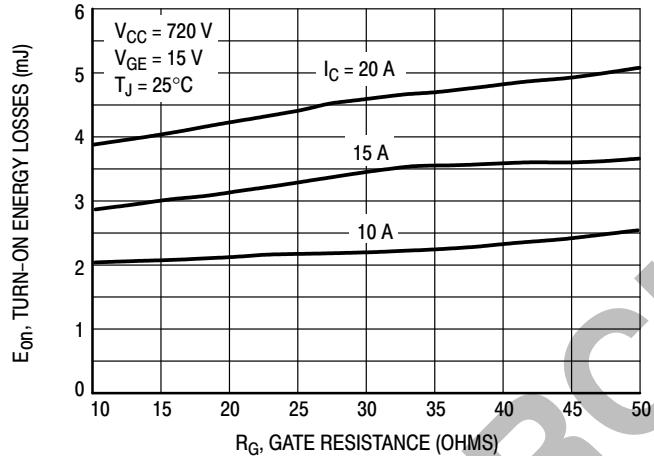


Figure 7. Turn-On Losses versus Gate Resistance

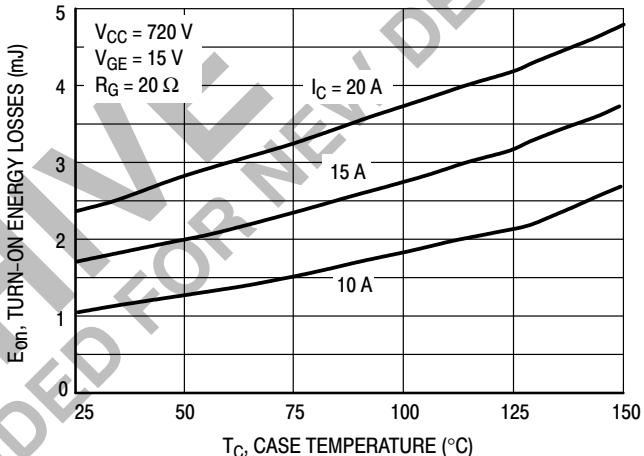


Figure 8. Turn-On Losses versus Case Temperature

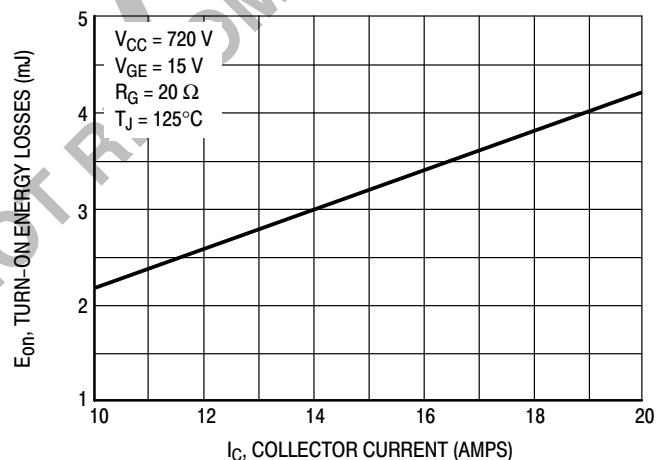
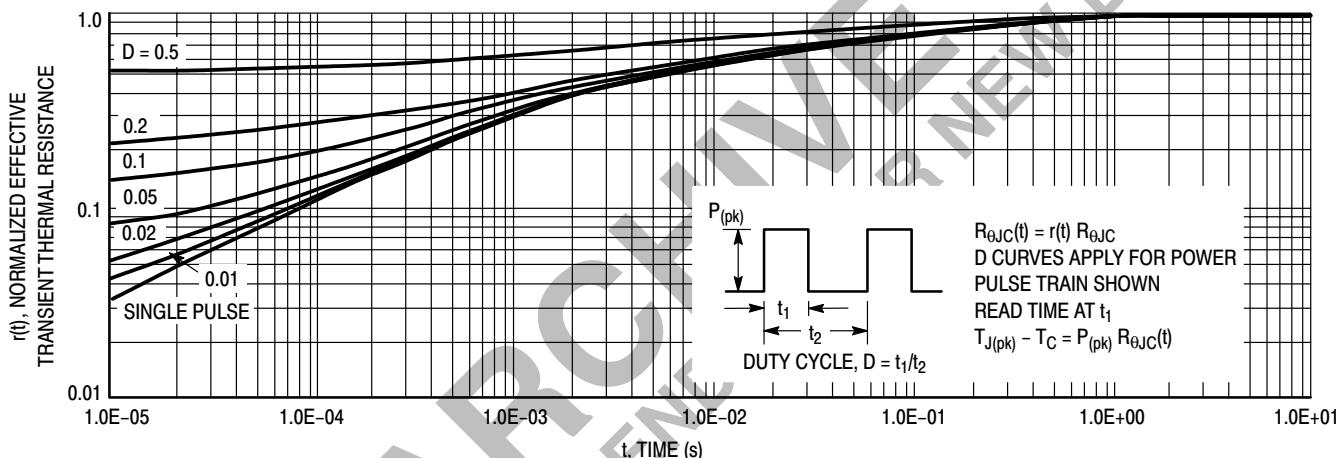
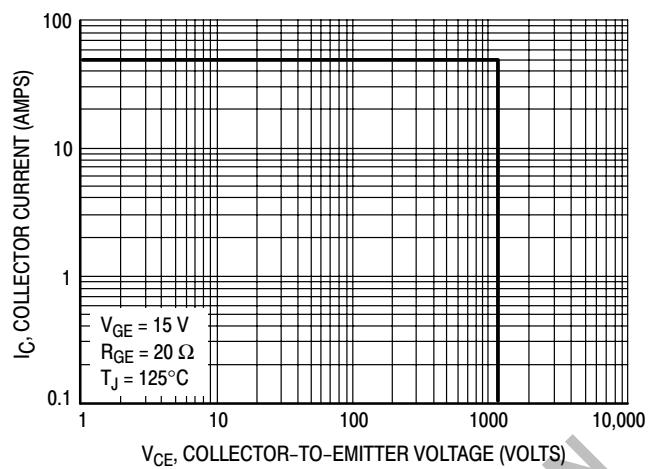
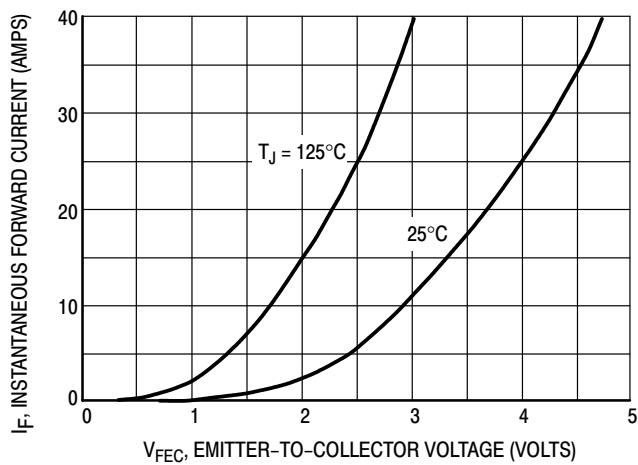
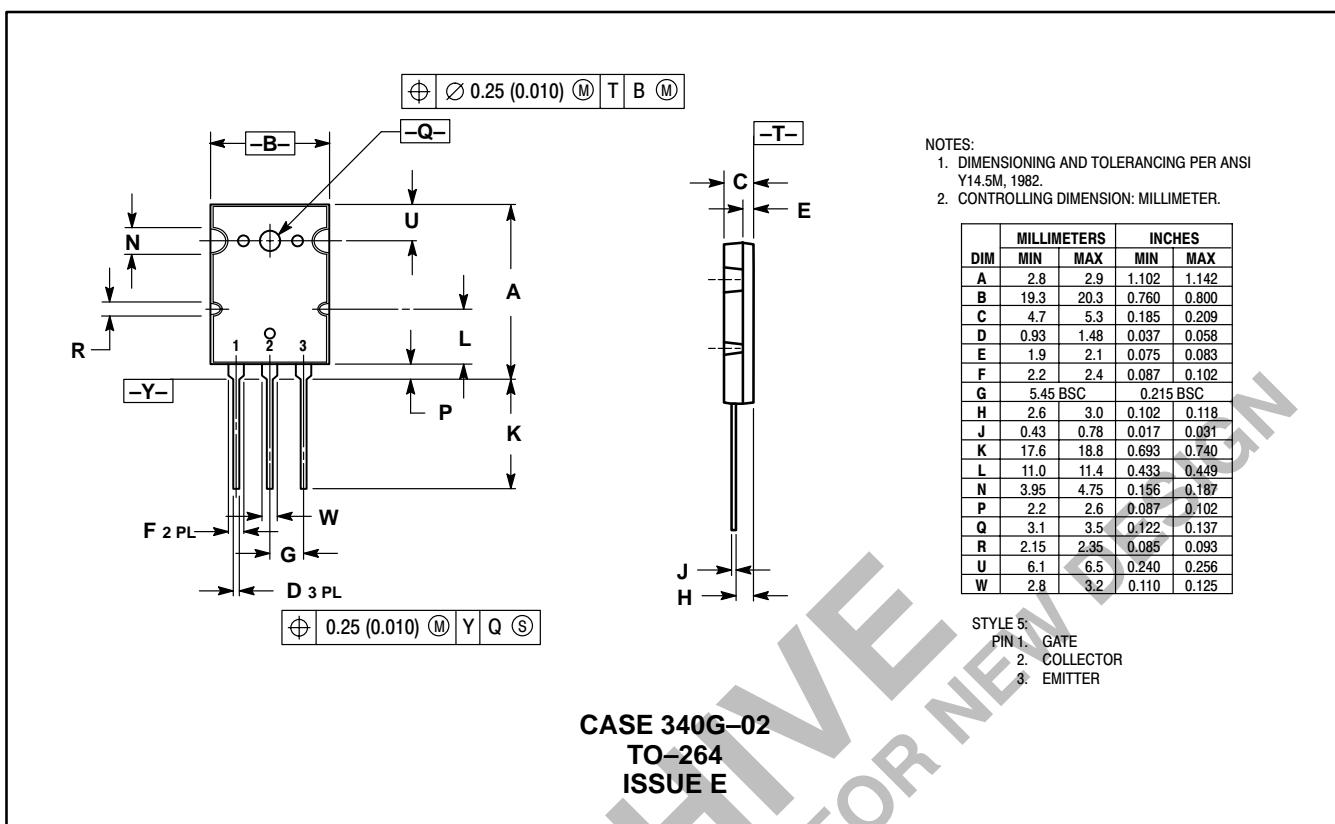


Figure 9. Turn-On Losses versus Collector Current



PACKAGE DIMENSIONS



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